

#### **Features**

Complementary Pair.

One 2SK2412K-Type NPN.

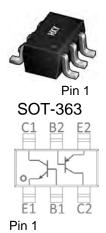
One 2SA1037AK-Type PNP.

Transistor elements independent, eliminating interference

Mounting cost and area can be cut in half.

### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HUMZ1NTR	SOT-363	Z1	3000



#### Maxmim Ratings (Ta=25 unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current	150	mA
Pc	Collector Power Dissipation	150	mW
R <sub>ΘJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction And Storage Temperature Range	-55~+150	${\mathbb C}$

## 2SAK2412 Electrcal Charcteristics (Ta=25 unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Туе	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =50μΑ,I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA,I <sub>B</sub> =0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =50μA,I <sub>C</sub> =0	7			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =60V,I <sub>E</sub> =0			0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =7V,I <sub>C</sub> =0			0.1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =6V,I <sub>C</sub> =1mA	120		560	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA,I <sub>B</sub> =5mA			0.4	V
Transition frequency	f⊤	V <sub>CE</sub> =12V,I <sub>C</sub> =2mA,f=100MHz		180		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =12V,I <sub>E</sub> =0,f=1MHz		2.0	3.5	pF



# Maxmim Ratings (Ta=25 unless otherwise noted)

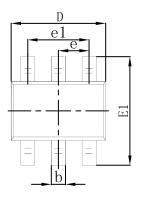
Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
VCEO	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-7	V
Ic	Collector Current	-150	mA
Pc	Collector Power Dissipation	150	mW
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient	625	°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction And Storage Temperature Range	-55~+150	$^{\circ}$

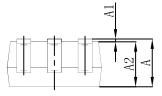
# 2SA1037AK Electrcal Charcteristics (Ta=25 unless otherwise specified)

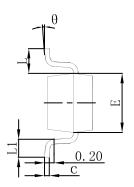
Parameter	Symbol	Test conditions	Min	Туе	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-50μA,I <sub>E</sub> =0	-60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA,I <sub>B</sub> =0	-50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-50μΑ,I <sub>C</sub> =0	-6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V,I <sub>E</sub> =0			-0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-6V,I <sub>C</sub> =0			-0.1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-6V,I <sub>C</sub> =-1mA	120		560	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-50mA,I <sub>B</sub> =-5mA			-0.5	>
Transition frequency	f⊤	V <sub>CE</sub> =-12V,I <sub>C</sub> =-2mA,f=100MHz		140		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-12V,I <sub>E</sub> =0,f=1MHz			5	pF



## **SOT-363 Package Outline Dimensions**

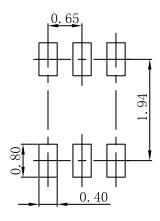






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650	) TYP	0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525	REF	0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

# **SOT-363 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.



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